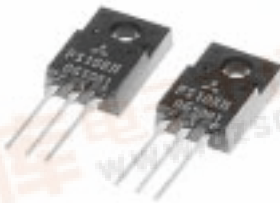


MITSUBISHI Nch POWER MOSFET

FS10KM-06

HIGH-SPEED SWITCHING USE

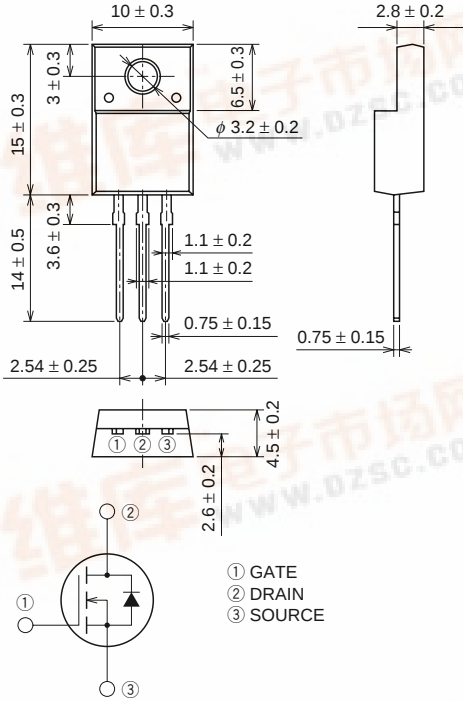
FS10KM-06



- 10V DRIVE
- V_{DSS} 60V
- r_{DS} (ON) (MAX) 78mΩ
- I_D 10A
- Integrated Fast Recovery Diode (TYP.) 55ns
- V_{iso} 2000V

OUTLINE DRAWING

Dimensions in mm



TO-220FN

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	V _{GS} = 0V	60	V
V _{GSS}	Gate-source voltage	V _{DS} = 0V	±20	V
I _D	Drain current		10	A
I _{DM}	Drain current (Pulsed)		40	A
I _{DA}	Avalanche drain current (Pulsed)	L = 100μH	10	A
I _S	Source current		10	A
I _{SM}	Source current (Pulsed)		40	A
P _D	Maximum power dissipation		20	W
T _{ch}	Channel temperature		-55 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C
V _{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

FS10KM-06

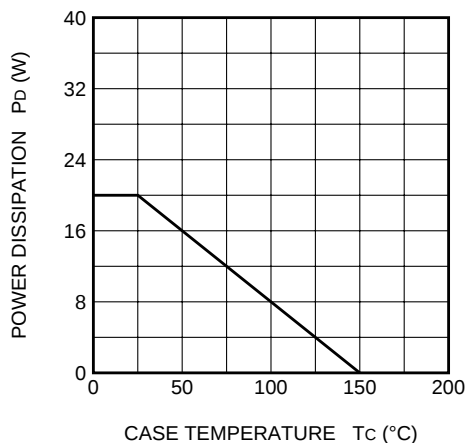
HIGH-SPEED SWITCHING USE

ELECTRICAL CHARACTERISTICS (Tch = 25°C)

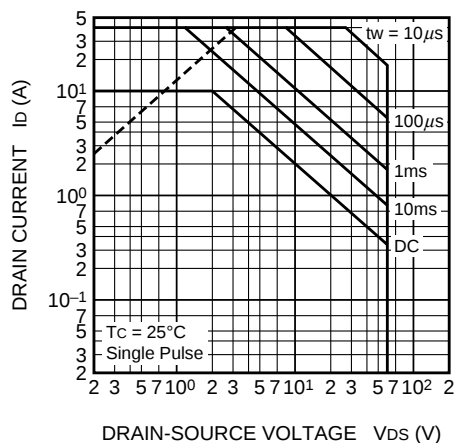
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	Id = 1mA, Vgs = 0V	60	—	—	V
IGSS	Gate-source leakage current	Vgs = ±20V, Vds = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	Vds = 60V, Vgs = 0V	—	—	0.1	mA
VGS(th)	Gate-source threshold voltage	Id = 1mA, Vds = 10V	2.0	3.0	4.0	V
rDS(ON)	Drain-source on-state resistance	Id = 5A, Vgs = 10V	—	58	78	mΩ
VDS(ON)	Drain-source on-state voltage	Id = 5A, Vgs = 10V	—	0.29	0.39	V
yfs	Forward transfer admittance	Id = 5A, Vds = 5V	—	9.0	—	S
Ciss	Input capacitance	Vds = 10V, Vgs = 0V, f = 1MHz	—	600	—	pF
Coss	Output capacitance		—	180	—	pF
Crss	Reverse transfer capacitance		—	60	—	pF
td(on)	Turn-on delay time	VDD = 30V, Id = 5A, Vgs = 10V, RGEN = RGS = 50Ω	—	18	—	ns
tr	Rise time		—	22	—	ns
td(off)	Turn-off delay time		—	30	—	ns
tf	Fall time		—	17	—	ns
VSD	Source-drain voltage	Is = 5A, Vgs = 0V	—	1.0	1.5	V
Rth(ch-c)	Thermal resistance	Channel to case	—	—	6.25	°C/W
trr	Reverse recovery time	Is = 10A, dis/dt = -100A/μs	—	55	—	ns

PERFORMANCE CURVES

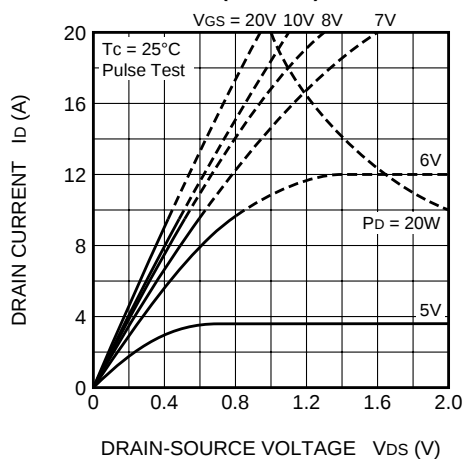
POWER DISSIPATION DERATING CURVE



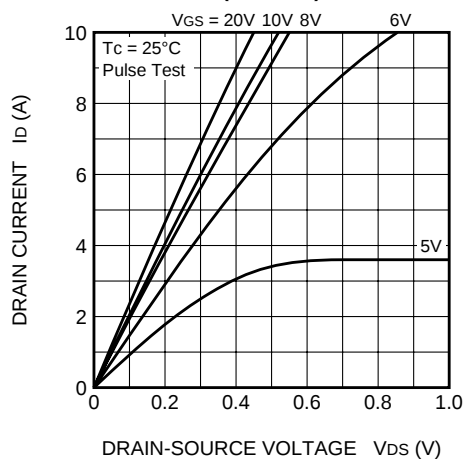
MAXIMUM SAFE OPERATING AREA



OUTPUT CHARACTERISTICS (TYPICAL)

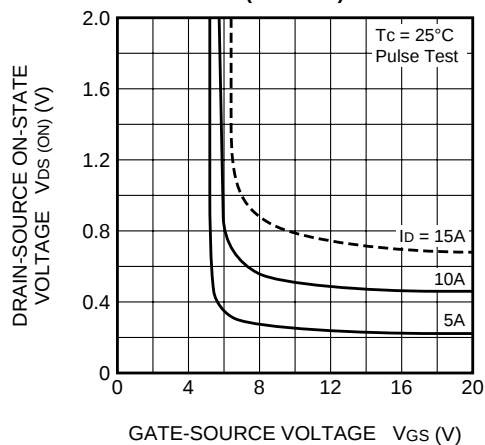
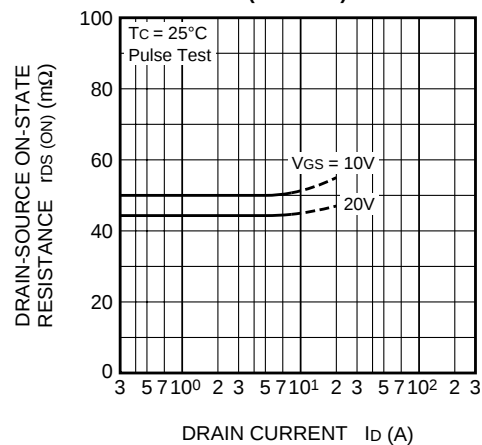
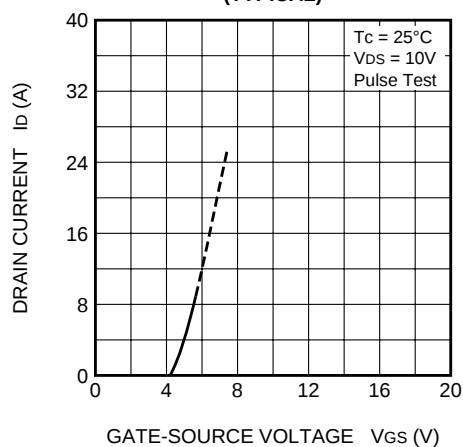
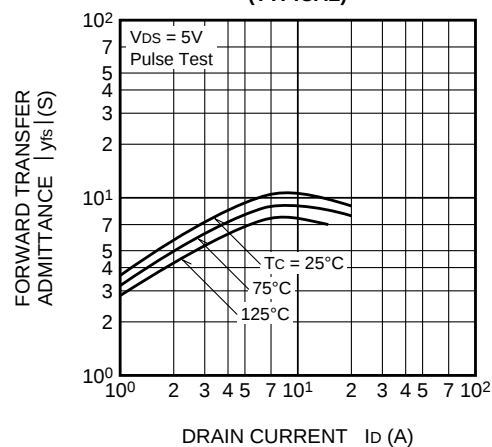
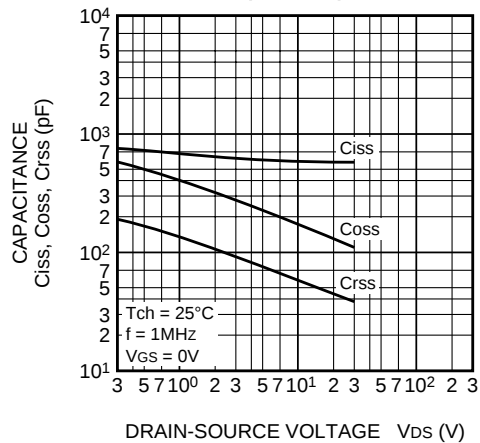
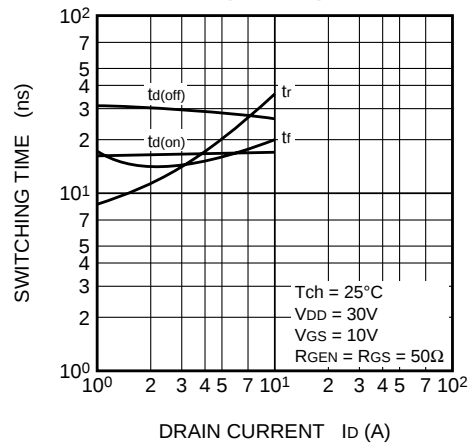


OUTPUT CHARACTERISTICS (TYPICAL)

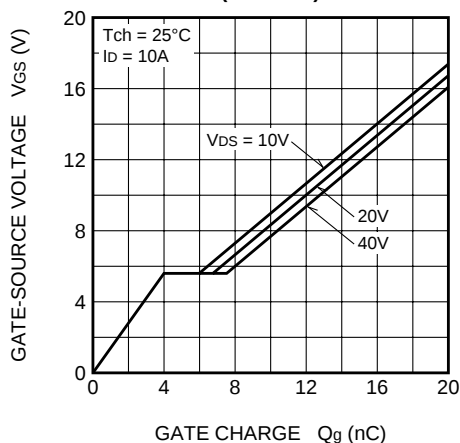


FS10KM-06

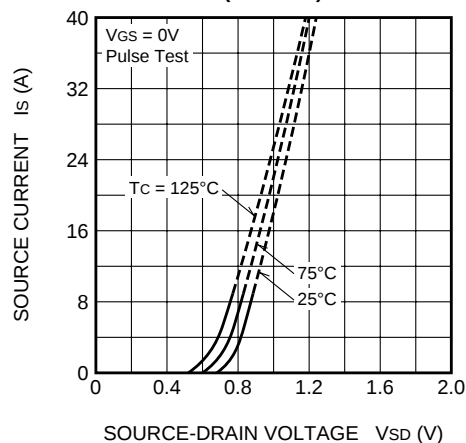
HIGH-SPEED SWITCHING USE

ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)TRANSFER CHARACTERISTICS
(TYPICAL)FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)CAPACITANCE VS.
DRAIN-SOURCE VOLTAGE
(TYPICAL)SWITCHING CHARACTERISTICS
(TYPICAL)

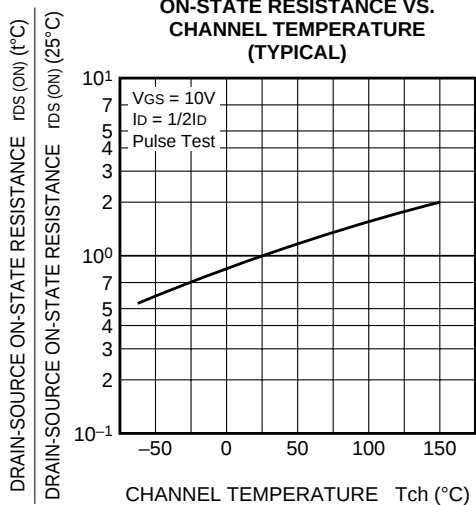
GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)



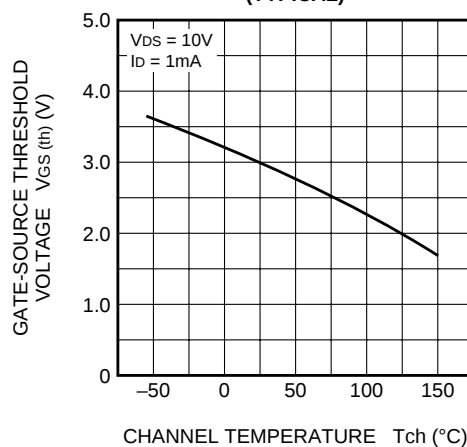
SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



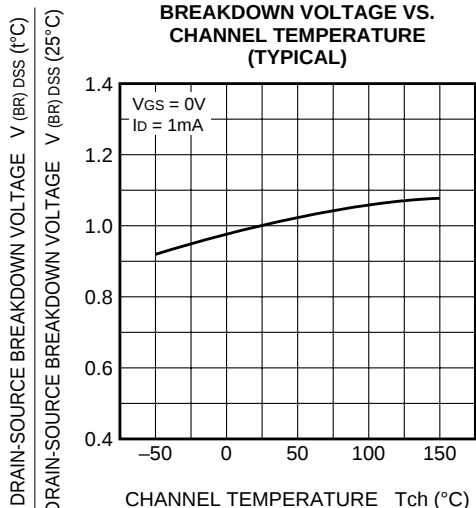
ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)



THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)



BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)



TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS

